

**Features**

- Dynamic random access memory 262144 x 1 bit manufactured using a CMOS technology
- RAS access times 70 ns, 80 ns
- TTL-compatible
- Three-state output
- 256 refresh cycles 4 ms refresh cycle time
- FAST PAGE MODE
- Operating modes: Read, Write, Read - Write,  $\overline{\text{RAS}}$  only Refresh, Hidden Refresh with address transfer
- Power Supply Voltage 5 V
- Packages PDIP16 (300 mil) SOJ20/26 (300 mil)
- Operating temperature range 0 to 70 °C
- Quality assessment according to CECC 90000, CECC 90100 and CECC 90112

**Description**

**Addressing**

The UD61256 is a dynamic Write-Read-memory with random access. FPM facilitates faster data operation with predefined row address. Via 9 address inputs the 18 address bits are transmitted into the internal address memories in a time-multiplex operation. The falling  $\overline{\text{RAS}}$ -edge takes over the row address. During  $\overline{\text{RAS}}$  Low, the column address together with the  $\overline{\text{CAS}}$  signal are taken over. The selection of one or more memory circuits can be made by activation of the  $\overline{\text{RAS}}$  input.

**Read-Write-Control**

The choice between Read or Write cycle is made at the  $\overline{\text{W}}$  input. HIGH at the  $\overline{\text{W}}$  input causes a Read cycle, meanwhile LOW leads to a Write cycle. Both  $\overline{\text{CAS}}$ -controlled and  $\overline{\text{W}}$ -controlled Write cycles are possible with activated RAS signal.

**Data Output Control**

The usual state of the data output is the High-Z state. Whenever  $\overline{\text{CAS}}$  is inactive (HIGH), Q will float (High-Z). Thus,  $\overline{\text{CAS}}$  functions as data output control.

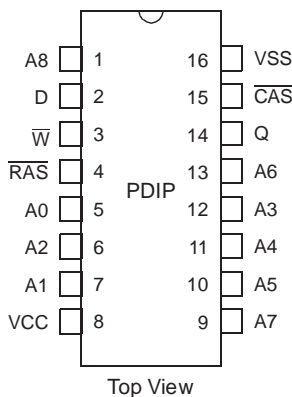
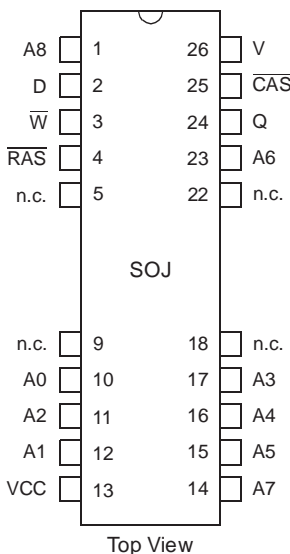
After access time, in case of a Read cycle, the output is activated, and it contains the logic „0“ or „1“.

Q is then valid until  $\overline{\text{CAS}}$  returns into to inactive state (HIGH).

The memory cycle being a Read, Read-Write or a Write cycle ( $\overline{\text{W}}$ -controlled), Q changes from High-Z state to the active state („0“ or „1“). After the access time the contents of the selected cell is available, except for the Write cycle.

The output remains active until  $\overline{\text{CAS}}$  becomes inactive, irrespective of  $\overline{\text{RAS}}$  becoming inactive or not. The memory cycle being a Write cycle ( $\overline{\text{CAS}}$ -controlled), the data output keeps its High-Z state throughout the whole cycle. This configuration makes Q fully controllable by the user merely through the timing of  $\overline{\text{W}}$ . The output storing the data, they remain valid from the end of access time until the start of another cycle.

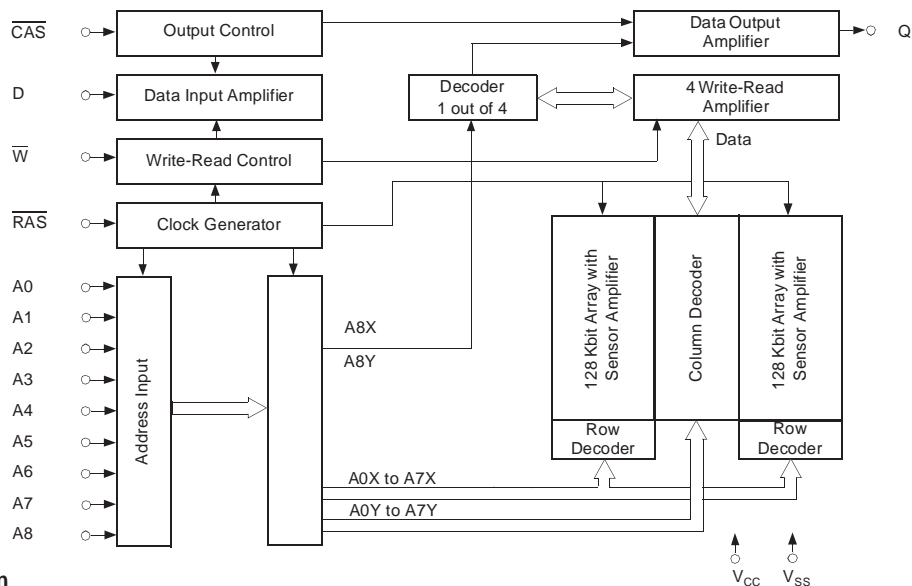
**Pin Configuration**



**Pin Description**

Signal Name	Signal Description
A0 - A8	Address Inputs
D	Data Input
$\overline{\text{W}}$	Read, Write Control
$\overline{\text{RAS}}$	Row Address Strobe
UCC	Power Supply Voltage
USS	Ground
$\overline{\text{CAS}}$	Column Address Strobe
Q	Data Output
n.c.	no connected

## Block Diagram



## Operation

Function		$\overline{\text{RAS}}$	$\overline{\text{CAS}}$	$\overline{\text{W}}$	Address		Data	
					R	C	D	Q
Stand-by		H	X	X	X	X	X	High-Z
Read		L	L	H	Row	Column	X	Output Data
Write		L	L	L	Row	Column	Input Data	High-Z
Read-Write		L	L	H → L	Row	Column	Input Data	Output Data
FPM Read	1st cycle	L	H → L	H	Row	Column	X	Output Data
	2nd cycle	L	H → L	H		Column	X	Output Data
FPM Write	1st cycle	L	H → L	L	Row	Column	Input Data	High-Z
	2nd cycle	L	H → L	L		Column	Input Data	High-Z
FPM Read-Write	1st cycle	L	H → L	H → L	Row	Column	Input Data	Output Data
	2nd cycle	L	H → L	H → L		Column	Input Data	Output Data
RAS only Refresh		L	H	X	Row		X	High-Z
HIDDEN Refresh*)	Read	L → H → L	L	H	Row	Column	X	Output Data
	Write	L → H → L	L	L	Row	Column	Input Data	High-Z

\*) Transfer of Refresh Address required

## Characteristics

All voltages are referenced to  $V_{SS} = 0$  V (ground).

All characteristics are valid in the power supply voltage range and operating temperature range indicated below.

Absolute Maximum Ratings	Symbol	Min.	Max.	Unit
Power Supply Voltage	$V_{CC}$	-0.5	7.0	V
Input Voltage <sup>1)</sup>	$V_I$	-1.0	7.0	V
Output Voltage <sup>1)</sup>	$V_O$	-1.0	7.0	V
Output Current	$I_O$	-50	50	mA
Power Dissipation	$P_D$		1	W
Operating Temperature	$T_a$	0	70	°C
Storage Temperature	$T_{stg}$	-55	125	°C

Remarks: see page 7

Recommended Operating Conditions	Symbol	Min.	Max.	Unit
Power Supply Voltage	$V_{CC}$	4.5	5.5	V
Input Low Voltage <sup>1)</sup>	$V_{IL}$	-1.0	0.8	V
Input High Voltage	$V_{IH}$	2.4	5.5	V

Remark: see page 7

Capacitances	Conditions	Symbol	Min.	Max.	Unit
Input Capacitance A0 to A8, D	$V_{CC} = 5.0$ V $V_I = V_{SS}$ $f = 1$ MHz $T_a = 25$ °C	$C_{11}$		6	pF
Input Capacitance RAS, CAS, W		$C_{12}$		7	pF
Output Capacitance		$C_O$		7	pF

All pins not under test must be connected with ground by capacitors.

Static Characteristics	Conditions	Symbol	Min.		Max.		Unit
			07	08	07	08	
Power Supply Current (average value of $\overline{\text{RAS}}\text{-}\overline{\text{CAS}}$ cycles) <sup>2)</sup>	$t_{cW} = t_{cWmin}$ $t_{cR} = t_{cRmin}$	$I_{CC1}$			70	60	mA
Refresh Current (average value of $\overline{\text{RAS}}$ cycles) <sup>2)</sup>	$t_{cW} = t_{cWmin}$ $t_{cR} = t_{cRmin}$ $\overline{\text{CAS}} = V_{IH}$	$I_{CC2}$			70	60	mA
FPM Current (average value of FPM cycles) <sup>2)</sup>	$t_{cPG} = t_{cPGmin}$ $\overline{\text{RAS}} = V_{IL}$	$I_{CC3}$			50	40	mA
Stand-by Current (TTL Level)	$\overline{\text{RAS}} = \overline{\text{CAS}}$ $= V_{IH}$	$I_{CC4}$			2	2	mA
Stand-by Current (CMOS Level)	$\overline{\text{RAS}} = \overline{\text{CAS}}$ $= V_{CC} - 0.2 \text{ V}$	$I_{CC5}$			1	1	mA
Output High Voltage	$I_{OH} = -5 \text{ mA}$	$V_{OH}$	2.4	2.4			V
Output Low Voltage	$I_{OL} = 4.2 \text{ mA}$	$V_{OL}$			0.4	0.4	V
Input Leakage Current at any input, all other pins = 0 V	$V_I = 0 \text{ V to } 5.5 \text{ V}$	$I_I$	-10	-10	10	10	$\mu\text{A}$
Output Leakage Current Q = High-Z	$V_O = 0 \text{ V to } 5.5 \text{ V}$ $\overline{\text{RAS}} = \overline{\text{CAS}}$ $= V_{IH}$	$I_O$	-10	-10	10	10	$\mu\text{A}$

Remarks: see page 7

Dynamic Characteristics	3)	Symbol		Min.		Max.		Unit
		Alt.	IEC	07	08	07	08	
<input type="checkbox"/> ALL CYCLES								
Transition Time (Rise and Fall)	4)	$t_T$	$t_t$	3	3	50	50	ns
$\overline{\text{RAS}}$ Precharge Time		$t_{RP}$	$t_{w(\text{RASH})}$	50	60			ns
CAS Precharge Time		$t_{CP}$	$t_{w(\text{CASH})}$	10	10			ns
Row Address Set-up Time		$t_{ASR}$	$t_{su(\text{RA-RAS})}$	0	0			ns
Column Address Set-up Time		$t_{ASC}$	$t_{su(\text{CA-CAS})}$	0	0			ns
Row Address Hold Time		$t_{RAH}$	$t_h(\text{RAS-RA})$	10	10			ns
Column Address Hold Time		$t_{CAH}$	$t_h(\text{CAS-CA})$	15	15			ns
Column Address Hold Time ref. to $\overline{\text{RAS}}$		$t_{AR}$	$t_h(\text{RAS-CA})$	55	60			ns
Output Buffer Turn-off Delay	5)	$t_{OFF}$	$t_v(\text{CAS})$	0	0	20	20	ns
$\overline{\text{CAS}}$ to $\overline{\text{RAS}}$ Precharge Time		$t_{CRP}$	$t_{\text{CASH-RASL}}$	5	5			ns
$\overline{\text{RAS}}$ to Column Address Delay Time	6)	$t_{RAD}$	$t_{\text{RAS-CA}}$	15	15	35	40	ns
Column Address to $\overline{\text{RAS}}$ Lead Time		$t_{RAL}$	$t_{\text{CA-RASH}}$	35	40			ns
CAS to Output in Low-Z		$t_{CLZ}$	$t_{\text{CASL-QX}}$	0	0			ns
Refresh Period		$t_{REF}$	$t_{rf}$			4	4	ms
<input type="checkbox"/> READ								
Random Read Cycle Time	12)	$t_{RC}$	$t_{cR}$	130	150			ns
Access Time from $\overline{\text{RAS}}$	7), 8)	$t_{RAC}$	$t_a(\text{RAS})$			70	80	ns
Access Time from Column Address	7), 8)	$t_{AA}$	$t_a(\text{CA})$			35	40	ns
Access Time from $\overline{\text{CAS}}$	7), 8)	$t_{CAC}$	$t_a(\text{CAS})$			20	20	ns
$\overline{\text{RAS}}$ Pulse Width		$t_{RAS}$	$t_w(\text{RASL})$	70	80	10000	10000	ns
CAS Pulse Width		$t_{CAS}$	$t_w(\text{CASL})$	20	20	10000	10000	ns
Read Command Set-up Time		$t_{RCS}$	$t_{su(\text{R-CAS})}$	0	0			ns
Read Command Hold Time ref. to $\overline{\text{RAS}}$	9)	$t_{RRH}$	$t_h(\text{RAS-R})$	0	0			ns
Read Command Hold Time	9)	$t_{RCH}$	$t_h(\text{CAS-R})$	0	0			ns
$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Delay Time	6)	$t_{RCD}$	$t_{\text{RASL-CASL}}$	20	20	50	60	ns
CAS Hold Time		$t_{CSH}$	$t_{\text{RASL-CASH}}$	70	80			ns
$\overline{\text{RAS}}$ Hold Time		$t_{RSH}$	$t_{\text{CASL-RASH}}$	20	20			ns
<input type="checkbox"/> WRITE								
Random Write Cycle Time	12)	$t_{RC}$	$t_{cW}$	130	150			ns
$\overline{\text{RAS}}$ Pulse Width		$t_{RAS}$	$t_w(\text{RASL})$	70	80	10000	10000	ns
CAS Pulse Width		$t_{CAS}$	$t_w(\text{CASL})$	20	20	10000	10000	ns
Write Command Pulse Width		$t_{WP}$	$t_w(\text{W})$	15	15			ns

Remarks: see page 7

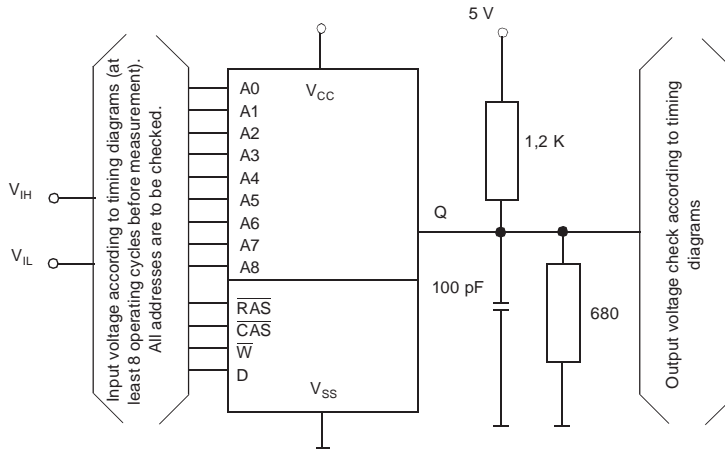
Dynamic Characteristics	3)	Symbol		Min.		Max.		Unit
		Alt.	IEC	07	08	07	08	
<input type="checkbox"/> WRITE (continuation)								
Write Command Set-up Time	10)	$t_{WCS}$	$t_{su(W-CAS)}$	0	0			ns
Data Set-up Time ref. to $\overline{CAS}$	11)	$t_{DS}$	$t_{su(D-CAS)}$	0	0			ns
Data Set-up Time ref. to $\overline{W}$	11)	$t_{DS}$	$t_{su(D-W)}$	0	0			ns
Write Command Hold Time		$t_{WCH}$	$t_{h(CAS-W)}$	15	15			ns
Write Command to RAS Lead Time		$t_{RWL}$	$t_{h(W-RAS)}$	20	20			ns
Write Command to CAS Lead Time		$t_{CWL}$	$t_{h(W-CAS)}$	20	20			ns
Data Hold Time ref. to RAS		$t_{DHR}$	$t_{h(RAS-D)}$	55	60			ns
Data Hold Time ref. to $\overline{CAS}$		$t_{DH}$	$t_{h(CAS-D)}$	15	15			ns
Data Hold Time ref. to $\overline{W}$		$t_{DH}$	$t_{h(W-D)}$	15	15			ns
$\overline{RAS}$ to $\overline{CAS}$ Delay Time	6)	$t_{RCD}$	$t_{RASL-CASL}$	20	20	50	60	ns
$\overline{CAS}$ Hold Time		$t_{CSH}$	$t_{RASL-CASH}$	70	80			ns
$\overline{RAS}$ Hold Time		$t_{RSH}$	$t_{CASL-RASH}$	20	20			ns
<input type="checkbox"/> READ-WRITE								
Read-Write Cycle Time	12)	$t_{RWC}$	$t_{cRW}$	155	175			ns
$\overline{RAS}$ Pulse Width		$t_{RAS}$	$t_{w(RASL)RW}$	95	105	10000	10000	ns
$\overline{CAS}$ Pulse Width		$t_{CAS}$	$t_{w(CASL)RW}$	45	45	10000	10000	ns
$\overline{CAS}$ Hold Time		$t_{CSH}$	$t_{(RASL-CASH)RW}$	95	105			ns
$\overline{RAS}$ to $\overline{WRITE}$ Delay Time	10)	$t_{RWD}$	$t_{RAS-W}$	70	80			ns
$\overline{CAS}$ to $\overline{WRITE}$ Delay Time	10)	$t_{CWD}$	$t_{CAS-W}$	20	20			ns
Column to $\overline{WRITE}$ Delay Time	10)	$t_{AWD}$	$t_{(CA-W)RW}$	35	40			ns
<input type="checkbox"/> FPM								
Fast Page Mode Cycle Time	12)	$t_{PC}$	$t_{cPG}$	50	50			ns
RAS Pulse Width		$t_{RASP}$	$t_{w(RASL)}$	70	80	100000	100000	ns
Access Time from $\overline{CAS}$ Precharge		$t_{CPA}$	$t_{a(CASH)}$	35	40			ns
<input type="checkbox"/> HIDDEN-REFRESH								
$\overline{CAS}$ Hold Time ( $\overline{CAS}$ before $\overline{RAS}$ Cycle)		$t_{CHR}$	$t_{RASL-CASH}$	15	15			ns

Remarks: see page 7

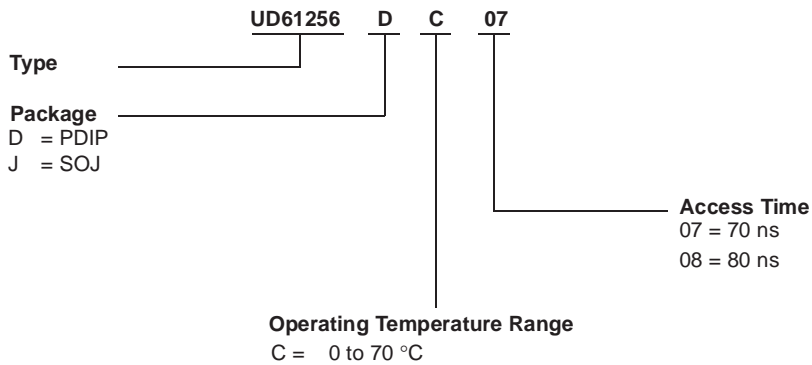
**Remarks:**

- 1) The Input Low Voltage must not drop below -0.3 V for more than 40 ns.
- 2) The current is inversely proportional to the cycle time; the max. current is measured in the shortest cycle time.
- 3) For test conditions see test configuration for functional test and timing diagrams.
- 4)  $V_{IHmin}$  and  $V_{ILmax}$  are reference levels for time measurement of the input signals; transition times are measured between  $V_{IH}$  and  $V_{IL}$ .
- 5)  $t_{v(CAS)}$  and  $t_{v(RAS)}$  define the time at which the data output goes to High-Z; this time is not related to any level.
- 6)  $t_{RAS-CASLmax}$  and  $t_{RAS-CA}$  are given as reference points only; they do not represent restrictive conditions.
- 7) The access time is determined by the three times  $t_{a(RAS)}$ ,  $t_{a(CAS)}$  and  $t_{a(CA)}$ :
  - if  $t_{RAS-CASL} < t_{RAS-CASLmax}$  and  $t_{RAS-CA} < t_{RAS-CAmax}$   $t_{a(RAS)}$  is valid,
  - if  $t_{RAS-CASL} > t_{RAS-CASLmax}$  and  $t_{su(CA-CAS)} < (t_{a(CA)max} - t_{a(CAS)max})$   $t_{a(CA)}$  is valid,
  - if  $t_{RAS-CASL} > t_{RAS-CASLmax}$  and  $t_{su(CA-CAS)} > (t_{a(CA)max} - t_{a(CAS)max})$   $t_{a(CAS)}$  is valid.
- 8) Measured with a load equivalent to 2 TTL loads.
- 9) In a READ cycle either  $t_{h(RAS-R)}$  or  $t_{h(CAS-R)}$  must be kept.
- 10)  $t_{su(W-CAS)}$ ,  $t_{RAS-W}$ ,  $t_{CAS-W}$  and  $t_{su(A)}$  do not represent restrictive parameters:
  - if  $t_{su(W-CAS)} \geq t_{su(W-CAS)min}$ , the cycle is a WRITE cycle ( $\overline{CAS}$ -controlled) and the data output remains in High-Z throughout the whole  $\overline{CAS}$  cycle,
  - if  $t_{CAS-W} > t_{CAS-Wmin}$ ,  $t_{RAS-W} > t_{RAS-Wmin}$  and  $t_{su(CA-W)RW} > t_{su(CA-W)RWmin}$ , the cycle is a READ-WRITE cycle and the content of the cell is available at the data output,
  - if none of these conditions is satisfied, the condition of the data output (at access time) is indeterminate, since a WRITE cycle ( $\overline{W}$ -controlled) is carried out.
- 11) These parameters refer to  $\overline{CAS}$  in the WRITE cycle ( $\overline{CAS}$ -controlled) and to  $\overline{W}$  during WRITE ( $\overline{W}$ -controlled) or to  $\overline{W}$  in the READ-WRITE cycle, resp.
- 12) The values of  $t_{cmin}$  are used for indication of the particular cycle time in which full function is guaranteed in the temperature range from 0 to 70 °C. Values below the one shown above may cause permanent damage to the component.

## Test Configuration for Functional Check



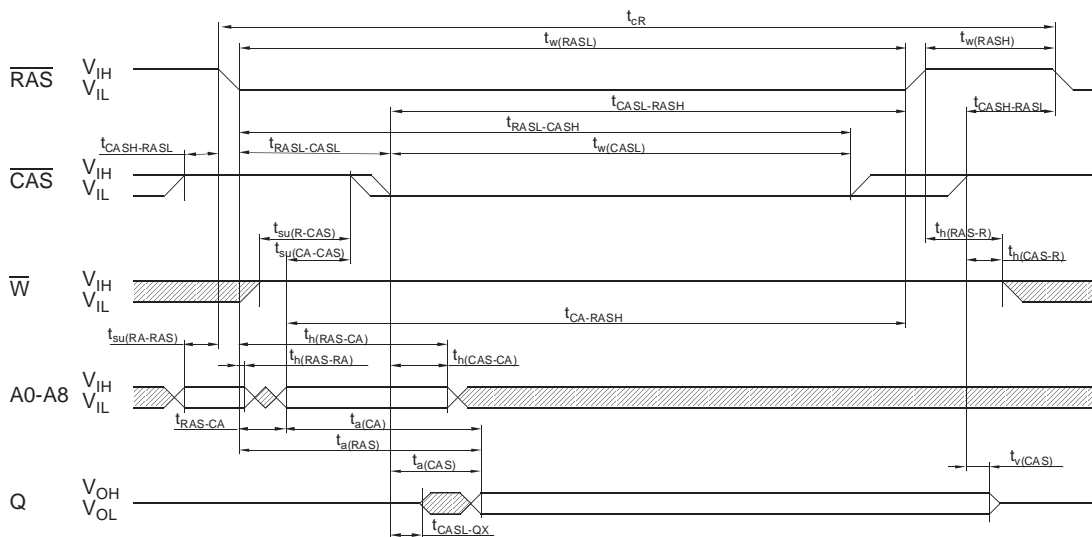
## IC Code Numbers



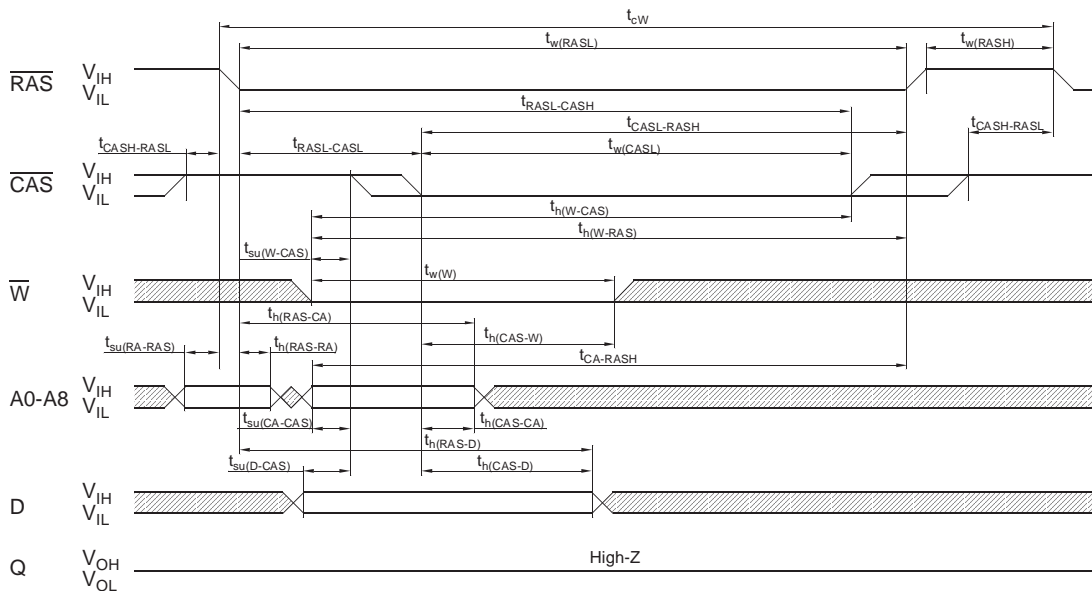
The date of manufacture is given by the 4 last digits of the mark, the 2 first digits indicating the year, and the last 2 digits the calendar week.



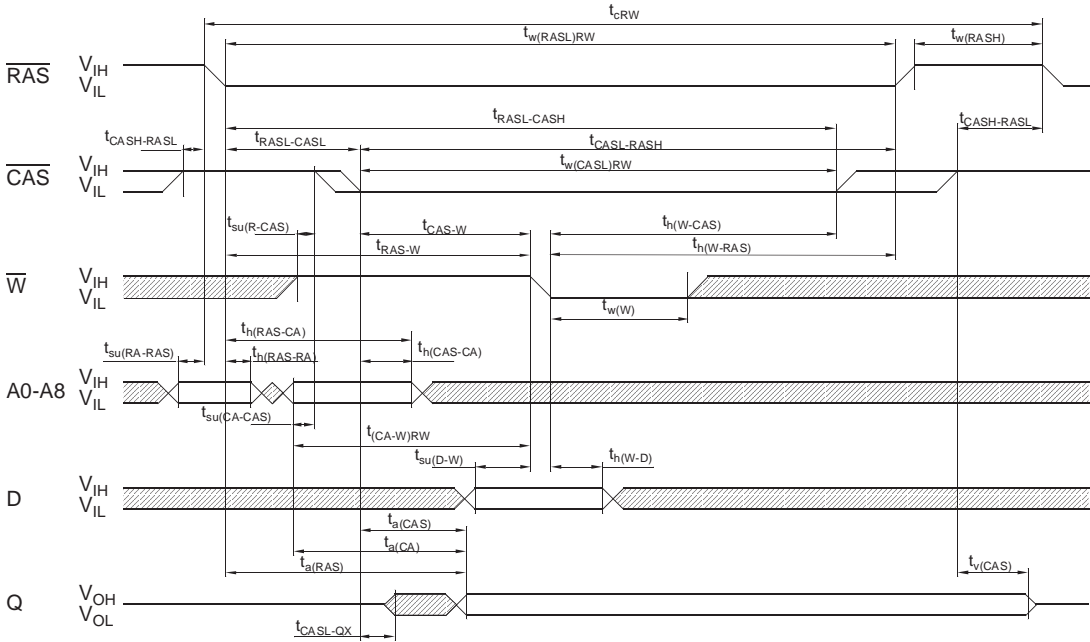
Read



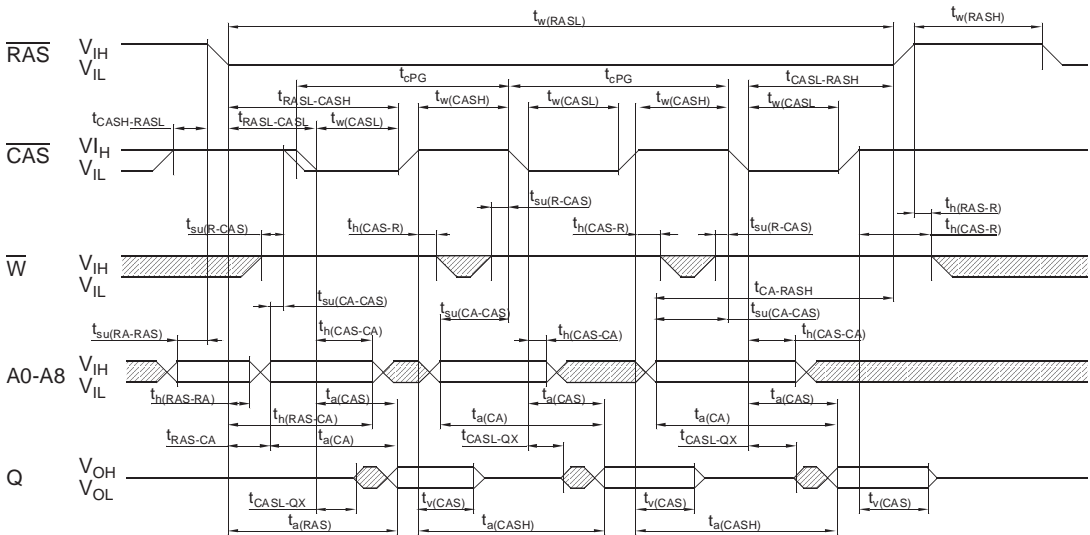
Write (CAS-controlled)



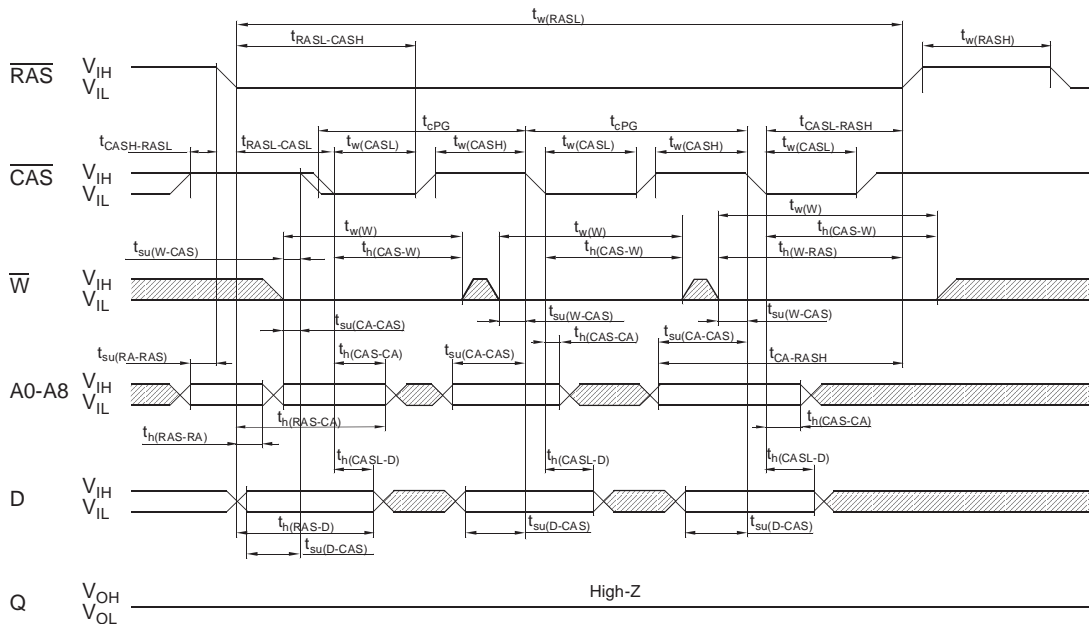
## Read-Write



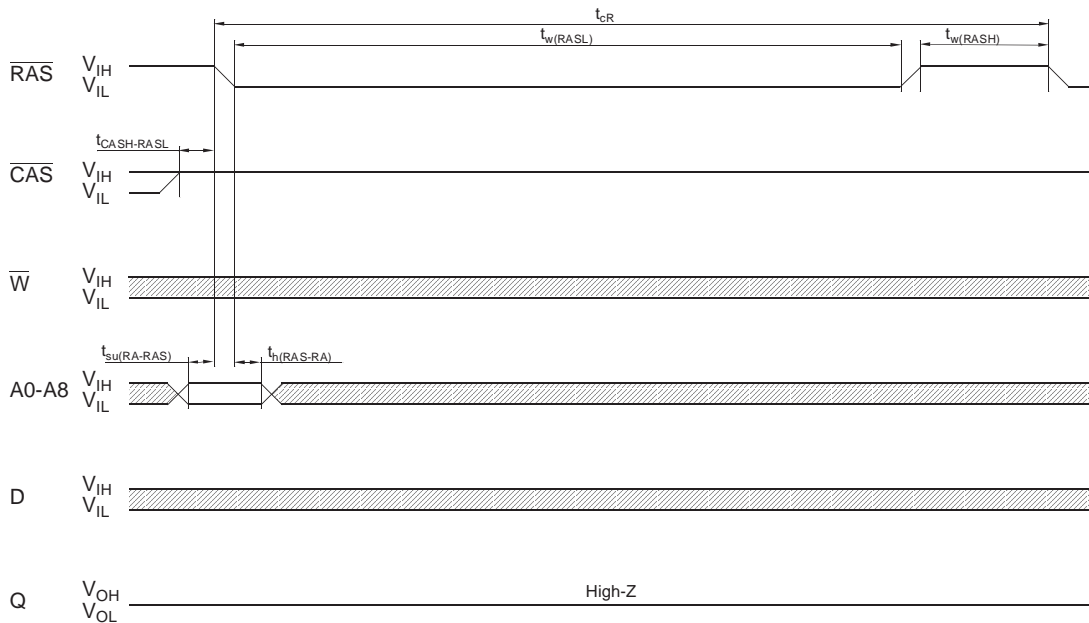
## FPM Read



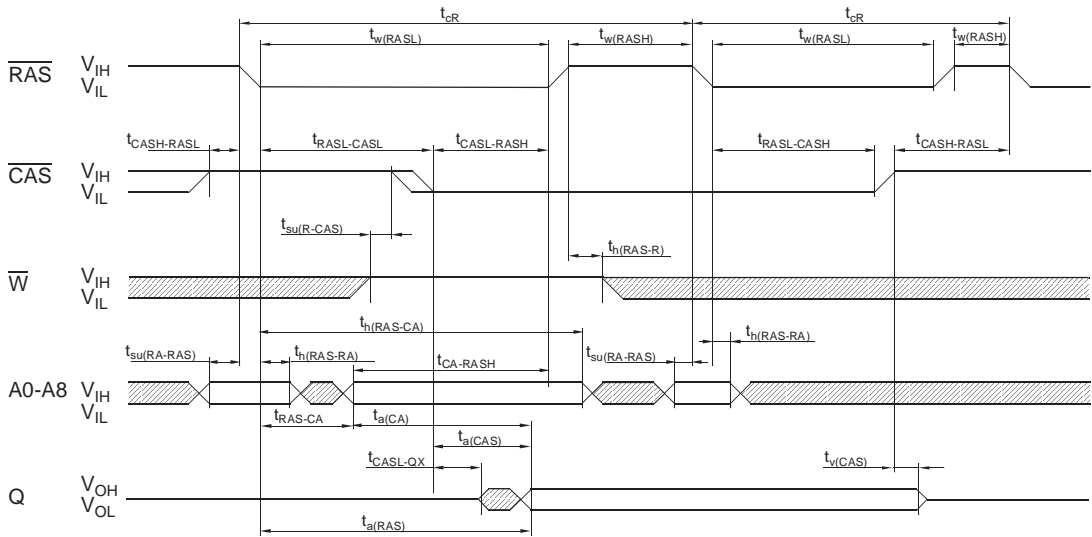
FPM Write ( $\overline{\text{CAS}}$ -controlled)



$\overline{\text{RAS}}$  only Refresh



## HIDDEN-Refresh with address transfer





Zentrum Mikroelektronik Dresden

## **Memory Products 1998 256K x 1 DRAM UD61256**

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